



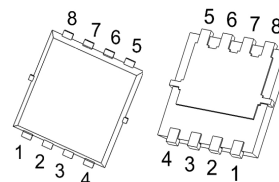
JIANGSU CHANGJING ELECTRONICS TECHNOLOGY CO., LTD

PDFNWB3.3×3.3-8L Plastic-Encapsulate MOSFETS

CJAB25SN06 N-Channel Power MOSFET

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
65V	13.5mΩ@10V	25A
	23.0mΩ@4.5V	

PDFNWB3.3×3.3-8L



DESCRIPTION

The CJAB25SN06 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications

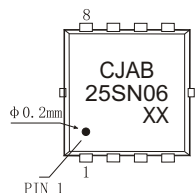
FEATURES

- High Power and current handing capability
- Load switch
- High density cell design for ultra low $R_{DS(ON)}$
- Lead free product is acquired
- Excellent package for good heat dissipation

APPLICATIONS

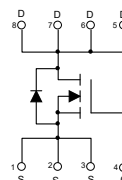
- SMPS and general purpose applications
- Hard switched and high frequency circuits
- Uninterruptible Power Supply
- Power management

MARKING



CJAB25SN06 = Part No.
Solid dot = Pin1 indicator
XX = Code

EQUIVALENT CIRCUIT



MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	65	V
Gate-Source Voltage	V_{GS}	+20/-12V	V
Continuous Drain Current	I_D ①	25	A
Pulsed Drain Current	I_{DM} ②	100	A
Power Dissipation	P_D ⑤	1.5	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$ ⑤	83.3	$^{\circ}\text{C/W}$
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	-55 ~+150	$^{\circ}\text{C}$
Lead Temperature for Soldering Purposes(1/8" from case for 10s)	T_L	260	$^{\circ}\text{C}$

MOSFET ELECTRICAL CHARACTERISTICS

$T_a=25^{\circ}\text{C}$ unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Off characteristics						
Drain-source breakdown voltage	V _{(BR) DSS}	V _{GS} = 0V, I _D =250μA	65			V
Zero gate voltage drain current	I _{DSS}	V _{DS} =65V, V _{GS} =0V			1	μA
Gate-body leakage current	I _{GSS}	V _{DS} =0V, V _{GS} =+20/-12V			±100	nA
On characteristics ③						
Gate-threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.0	1.5	2.5	V
Static drain-source on-sate resistance	R _{DS(on)}	V _{GS} =10V, I _D =12A		13.5	16	mΩ
		V _{GS} =4.5V, I _D =5A		23.0	30	mΩ
Forward transconductance	g _{Fs}	V _{DS} =10V, I _D =3A		4.7		S
Dynamic characteristics ③ ④						
Input capacitance	C _{iss}	V _{DS} = 30V, V _{GS} = 0V, f = 1MHz		648	1300	pF
Output capacitance	C _{oss}			239	380	
Reverse transfer capacitance	C _{rss}			22	60	
Gate resistance	R _g	f =1MHz		0.4		Ω
Switching characteristics ③ ④						
Total gate charge	Q _g	V _{DS} =30V, V _{GS} =10V, I _D =12A		13.8	22	nC
Gate-source charge	Q _{gs}			1.4	3	
Gate-drain charge	Q _{gd}			4.7	9	
Turn-on delay time	t _{d(on)}	V _{DS} =30V, I _D =1A, V _{GS} =10V, R _G =3.3Ω		8	16	ns
Turn-on rise time	t _r			12	24	
Turn-off delay time	t _{d(off)}			25	50	
Turn-off fall time	t _f			18	36	
Drain-Source Diode Characteristics						
Drain-source diode forward voltage	V _{SD} ③	V _{GS} =0V, I _S =10A			1.0	V
Continuous drain-source diode forward current	I _S ①				25	A
Pulsed drain-source diode forward current	I _{SM} ②				100	A

Notes:

1. $T_C = 25^{\circ}\text{C}$ Limited only by maximum temperature allowed.

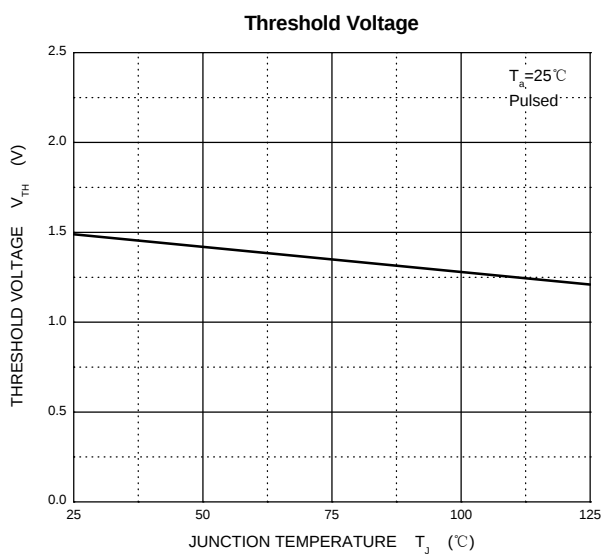
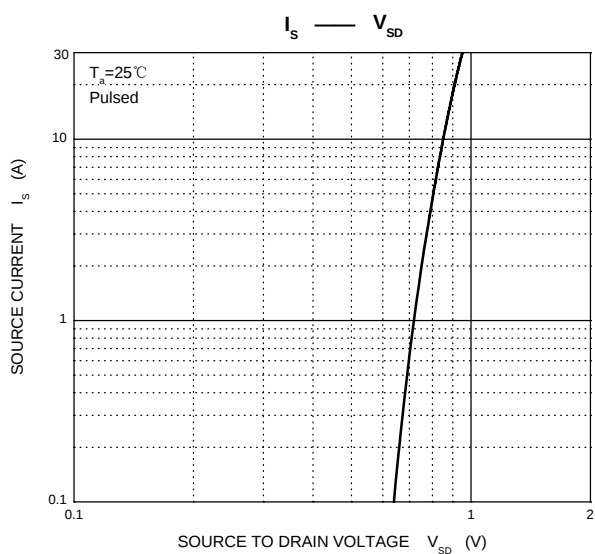
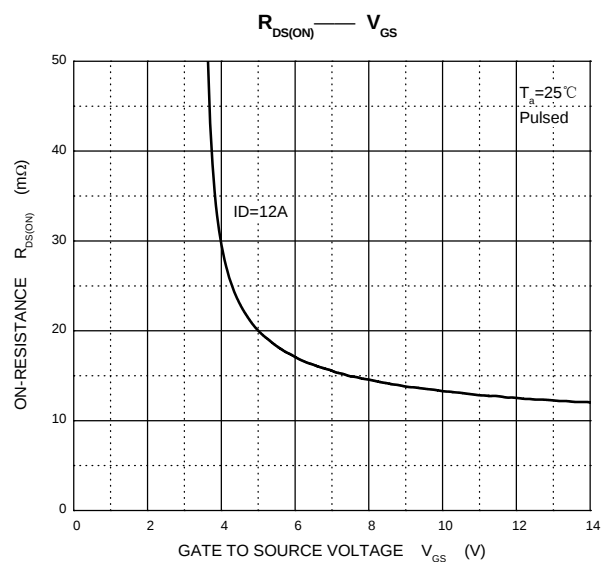
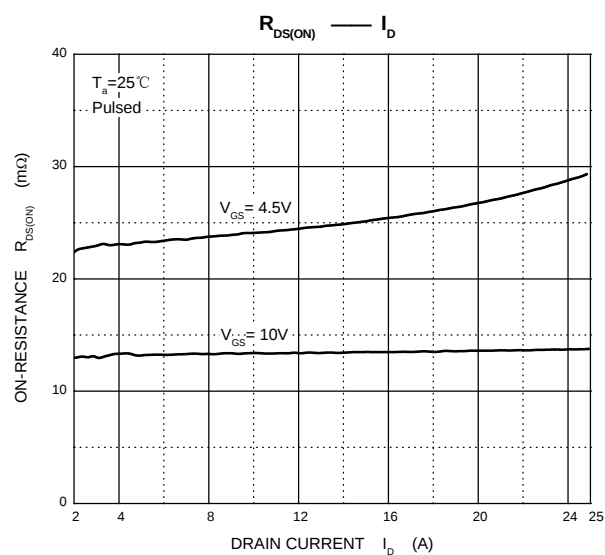
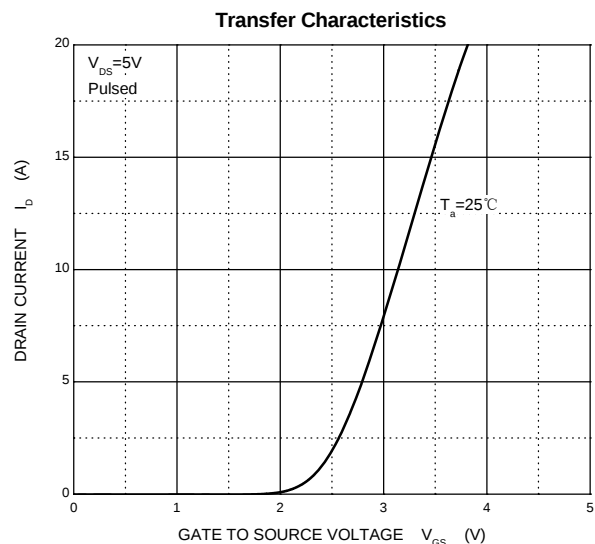
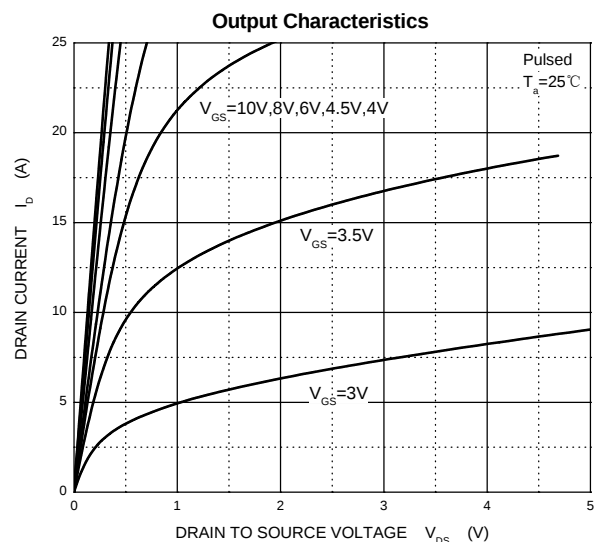
2. $P_W \leq 10\mu s$, Duty cycles $\leq 1\%$.

3. Pulse Test : Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.

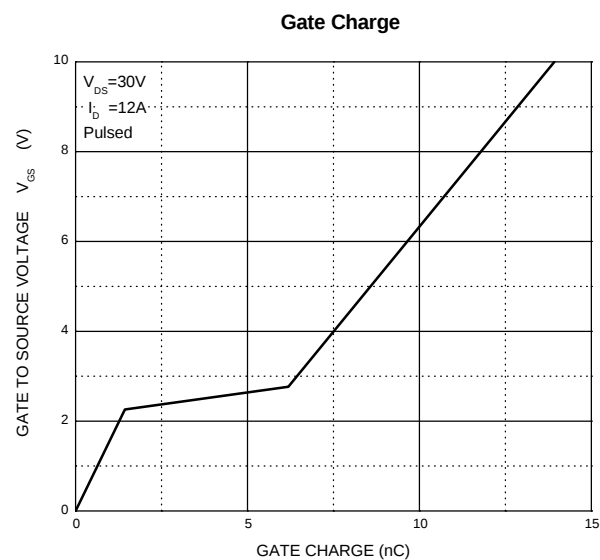
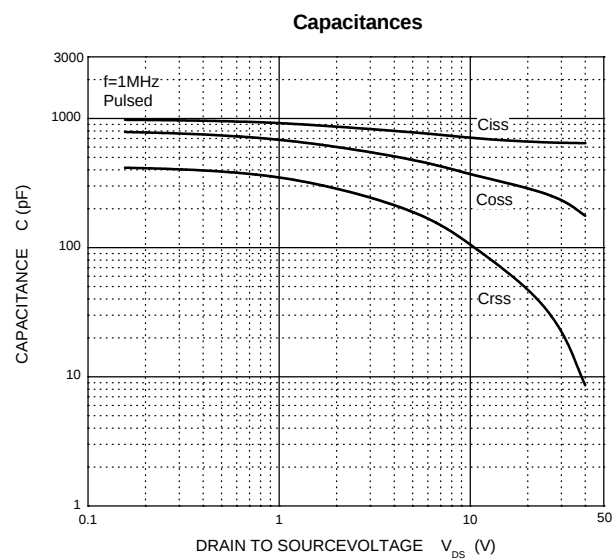
4. Guaranteed by design, not subject to production.

5. The value of $R_{\theta JA}$ is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_a = 25^{\circ}\text{C}$.

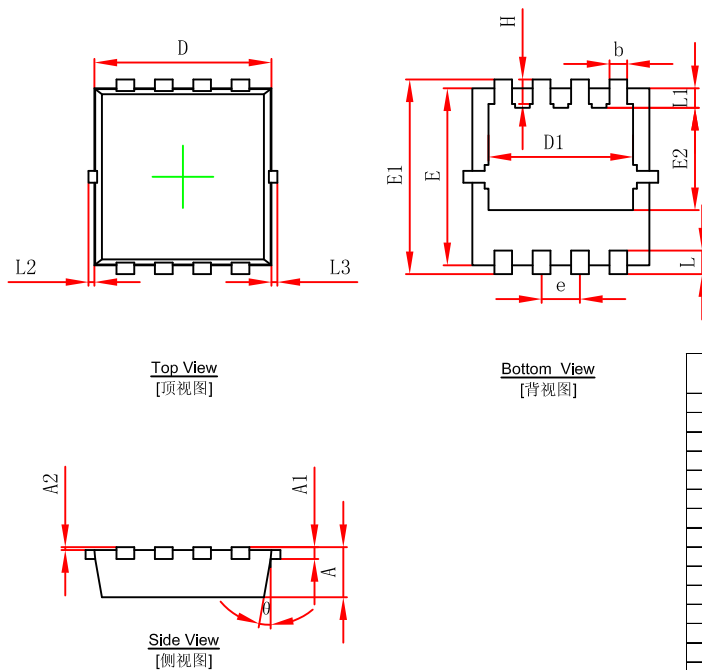
Typical Characteristics



Typical Characteristics

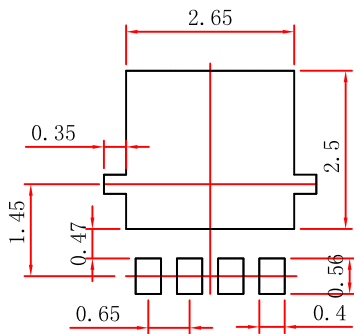


PDFNWB3.3x3.3-8L Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.650	0.850	0.026	0.033
A1	0.152 REF.		0.006 REF.	
A2	0~0.05		0~0.002	
D	2.900	3.100	0.114	0.122
D1	2.300	2.600	0.091	0.102
E	2.900	3.100	0.114	0.122
E1	3.150	3.450	0.124	0.136
E2	1.535	1.935	0.060	0.076
b	0.200	0.400	0.008	0.016
e	0.550	0.750	0.022	0.030
L	0.300	0.500	0.012	0.020
L1	0.180	0.480	0.007	0.019
L2	0~0.100		0~0.004	
L3	0~0.100		0~0.004	
H	0.315	0.515	0.012	0.020
θ	9°	13°	9°	13°

PDFNWB3.3x3.3-8L Suggested Pad Layout

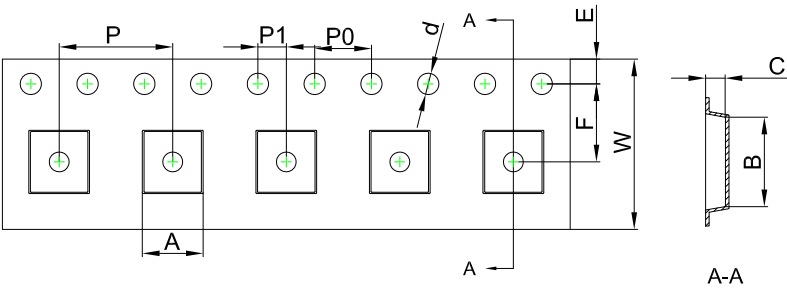


Note:
1.Controlling dimension:in millimeters.
2.General tolerance:±0.05mm.
3.The pad layout is for reference purposes only.

NOTICE

JSCJ reserves the right to make modifications,enhancements,improvements,corrections or other changes without further notice to any product herein. JSCJ does not assume any liability arising out of the application or use of any product described herein.

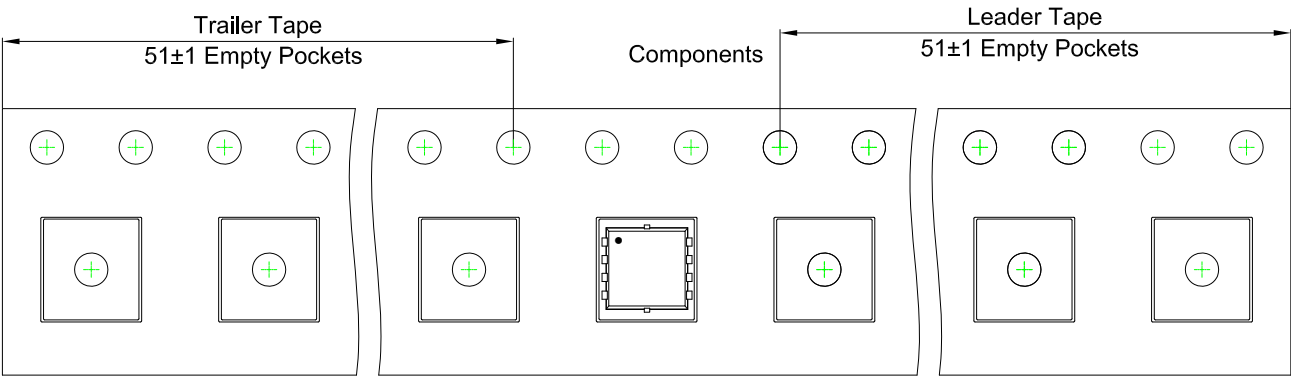
PDFNWB3.3×3.3-8L Embossed Carrier Tape



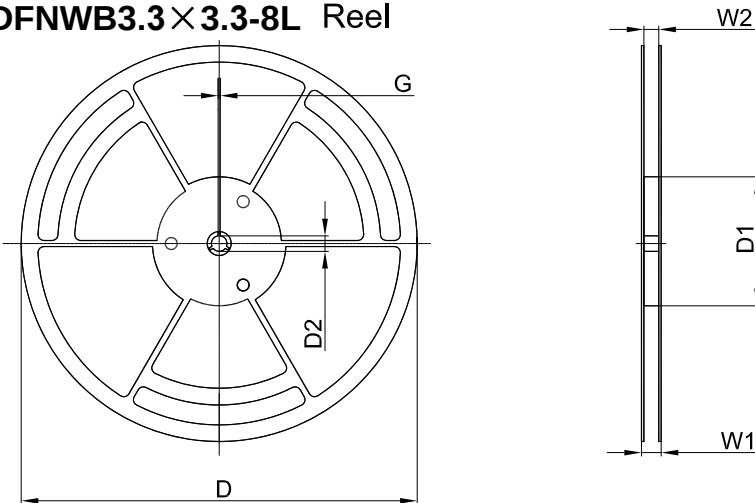
Packaging Description:
PDFNWB3.3×3.3-8L parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 5,000 units per 13" or 33.0 cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

Dimensions are in millimeter										
Pkg type	A	B	C	d	E	F	P0	P	P1	W
PDFNWB3.3×3.3-8L	3.55	3.55	1.10	Ø1.50	1.75	5.50	4.00	8.00	2.00	12.00

PDFNWB3.3×3.3-8L Tape Leader and Trailer



PDFNWB3.3×3.3-8L Reel



Dimensions are in millimeter						
Reel Option	D	D1	D2	G	W1	W2
13"Dia	Ø330.00	100.00	13.00	1.90	17.60	12.40

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)
5,000 pcs	13 inch	5,000 pcs	340×336×29	50,000 pcs	353×346×365